

NTMFS5830NL

Power MOSFET

40 V, 172 A, 2.3 mΩ

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	I_D	28	A
		22	
Power Dissipation $R_{\theta JA}$ (Note 1)	P_D	3.2	W
		2.0	
Continuous Drain Current $R_{\theta JC}$ (Note 1)	I_D	172	A
		138	
Power Dissipation $R_{\theta JC}$ (Note 1)	P_D	125	W
		80	
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	A
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +150	°C
Source Current (Body Diode)	I_S	172	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 50 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_L = 85 \text{ A}_{pk}$, $L = 0.1 \text{ mH}$, $R_G = 25 \Omega$)	E_{AS}	361	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain) (Note 1)	$R_{\theta JC}$	1.0	°C/W
Junction-to-Ambient Steady State (Note 1)	$R_{\theta JA}$	39	
Junction-to-Ambient Steady State (Note 2)	$R_{\theta JA}$	73	

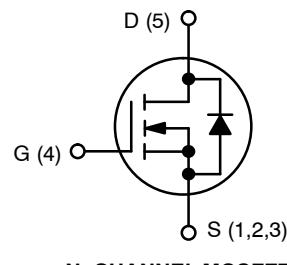
1. Surface-mounted on FR4 board using 1 sq-in pad (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using 0.155 in sq (100mm²) pad size.



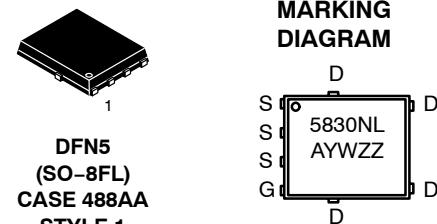
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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	2.3 mΩ @ 10 V	172 A
	3.6 mΩ @ 4.5 V	



N-CHANNEL MOSFET



A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping [†]
NTMFS5830NLT1G	DFN5 (Pb-Free)	1500/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTMFS5830NL

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$		40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}}/T_J$				32		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{GS}} = 0 \text{ V}$, $V_{\text{DS}} = 40 \text{ V}$	$T_J = 25^\circ\text{C}$		1		μA
			$T_J = 125^\circ\text{C}$			100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{\text{DS}} = 0 \text{ V}$, $V_{\text{GS}} = \pm 20 \text{ V}$				± 100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}$, $I_D = 250 \mu\text{A}$		1.0		3.0	V
Negative Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})}/T_J$				7.2		$\text{mV}/^\circ\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}$	$I_D = 20 \text{ A}$		1.7	2.3	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5 \text{ V}$	$I_D = 20 \text{ A}$		2.6	3.6	
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 5 \text{ V}$, $I_D = 10 \text{ A}$			38		S
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	C_{ISS}	$V_{\text{GS}} = 0 \text{ V}$, $f = 1 \text{ MHz}$, $V_{\text{DS}} = 25 \text{ V}$		5880			pF
Output Capacitance	C_{OSS}			750			
Reverse Transfer Capacitance	C_{RSS}			500			
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 10 \text{ V}$, $V_{\text{DS}} = 32 \text{ V}$; $I_D = 60 \text{ A}$		113			nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$	$V_{\text{GS}} = 4.5 \text{ V}$, $V_{\text{DS}} = 32 \text{ V}$; $I_D = 60 \text{ A}$		5.5			
Gate-to-Source Charge	Q_{GS}			19.5			
Gate-to-Drain Charge	Q_{GD}			32			
Plateau Voltage	V_{GP}			3.6			V
Gate Resistance	R_G			0.5			Ω
SWITCHING CHARACTERISTICS (Note 4)							
Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 4.5 \text{ V}$, $V_{\text{DS}} = 20 \text{ V}$, $I_D = 10 \text{ A}$, $R_G = 2.5 \Omega$		22			ns
Rise Time	t_r			32			
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			40			
Fall Time	t_f			27			
DRAIN-SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	$V_{\text{GS}} = 0 \text{ V}$, $I_S = 10 \text{ A}$	$T_J = 25^\circ\text{C}$		0.74	1.0	V
			$T_J = 125^\circ\text{C}$		0.58		
Reverse Recovery Time	t_{RR}	$V_{\text{GS}} = 0 \text{ V}$, $dI_S/dt = 100 \text{ A}/\mu\text{s}$, $I_S = 60 \text{ A}$		41			ns
Charge Time	t_a			19			
Discharge Time	t_b			19			
Reverse Recovery Charge	Q_{RR}			33			nC

3. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

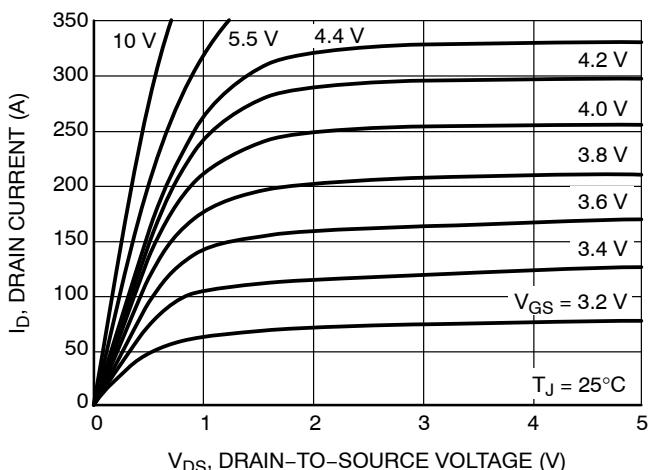


Figure 1. On-Region Characteristics

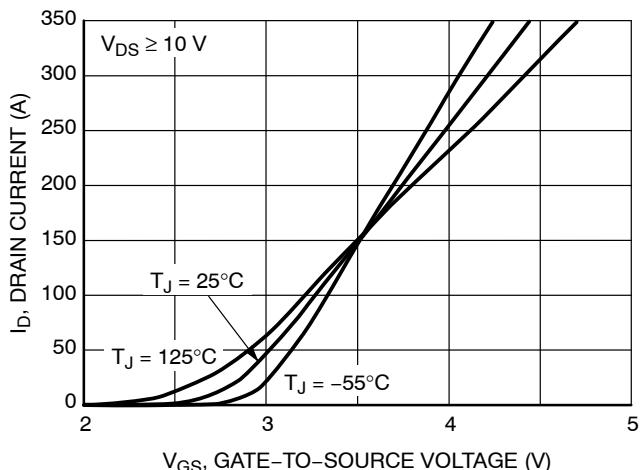


Figure 2. Transfer Characteristics

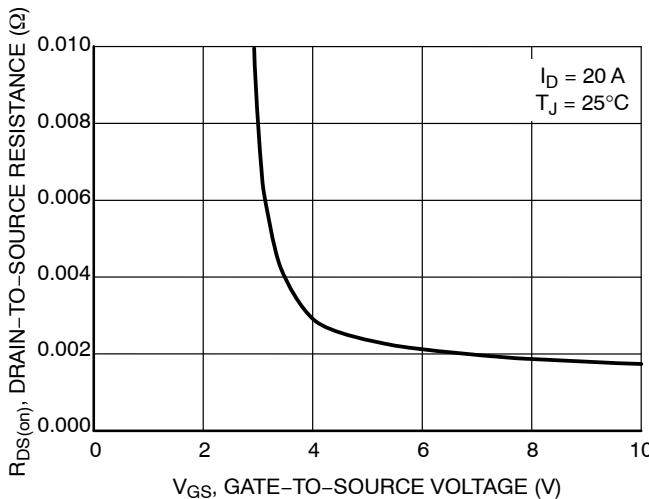


Figure 3. On-Resistance vs. Gate-to-Source Voltage

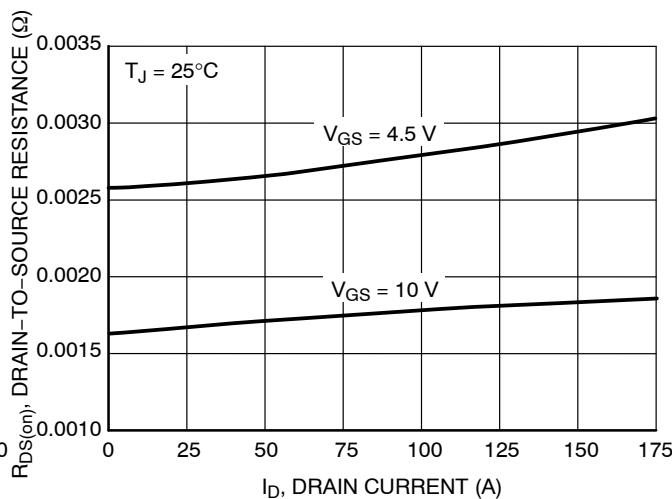


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

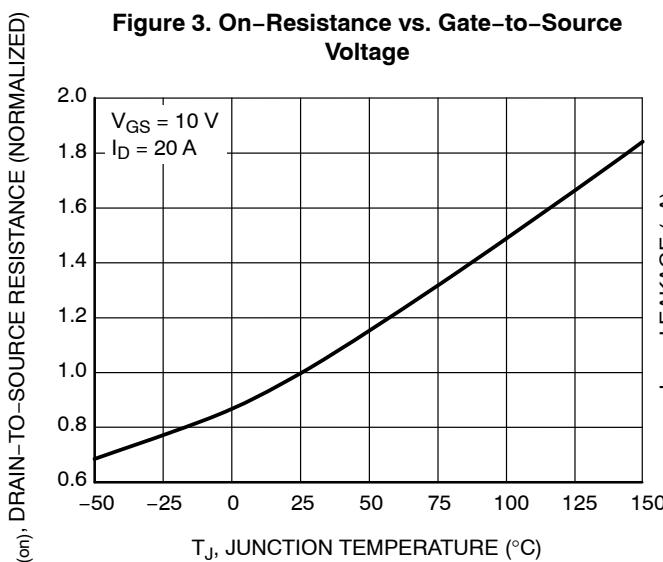


Figure 5. On-Resistance Variation with Temperature

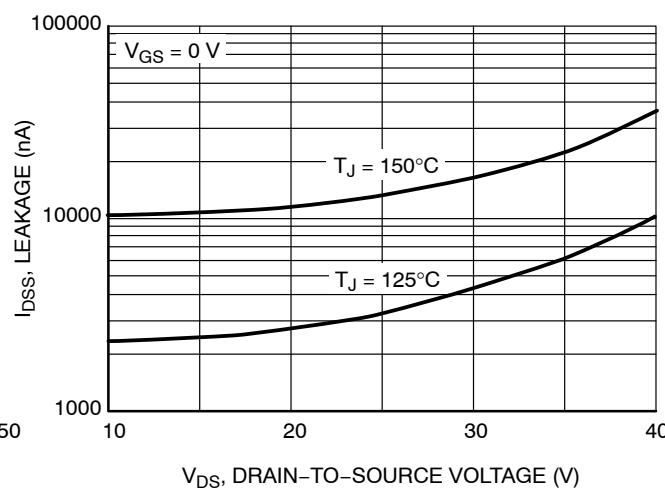
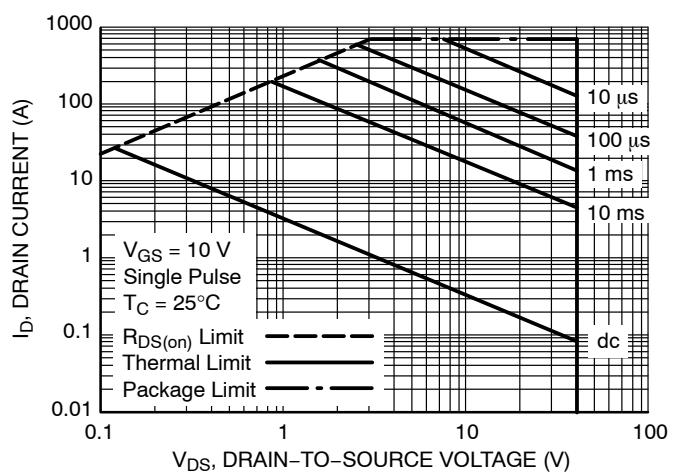
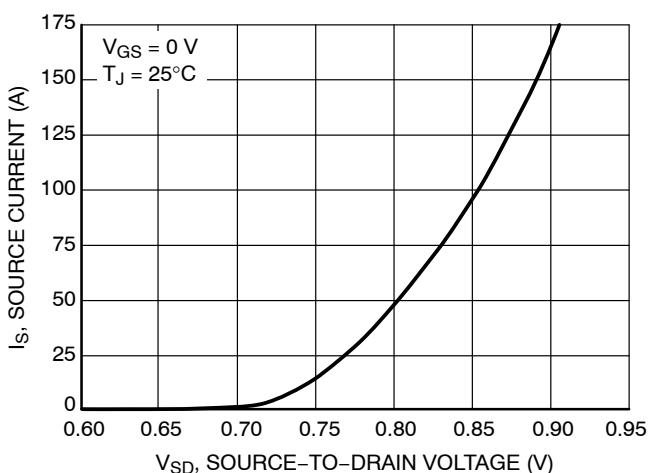
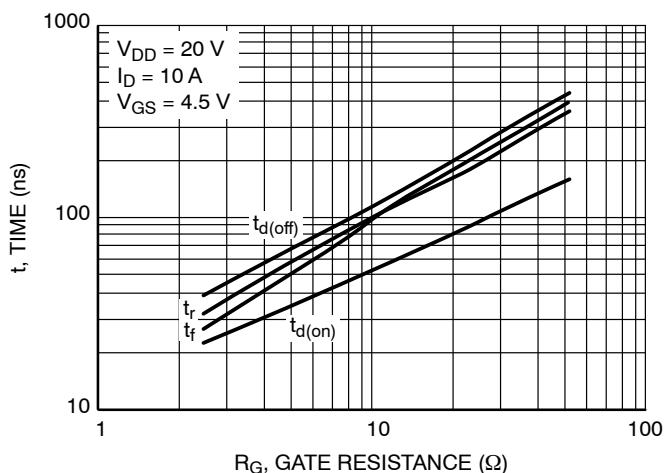
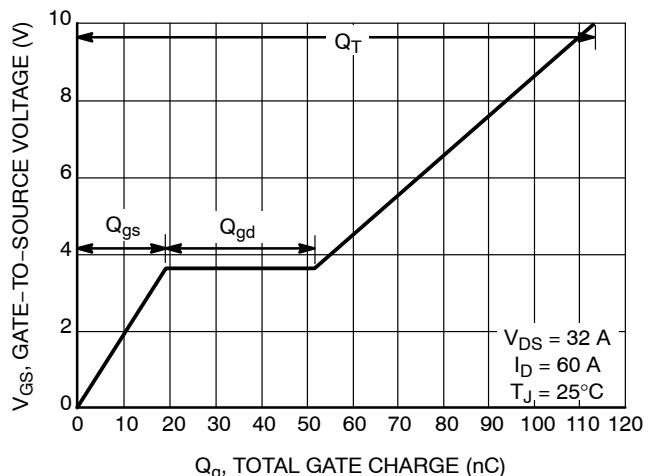
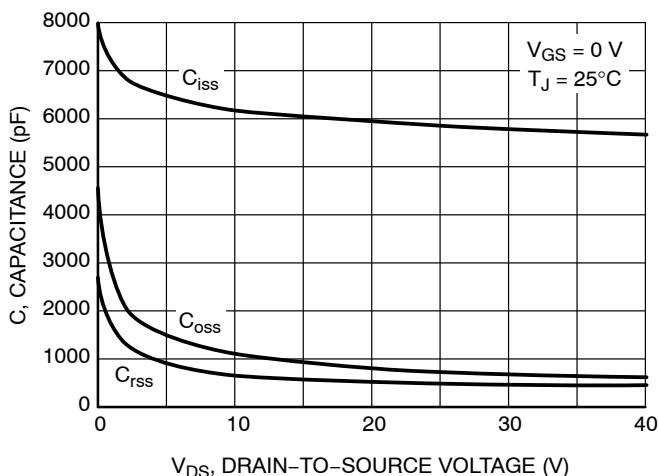


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS



NTMFS5830NL

TYPICAL CHARACTERISTICS

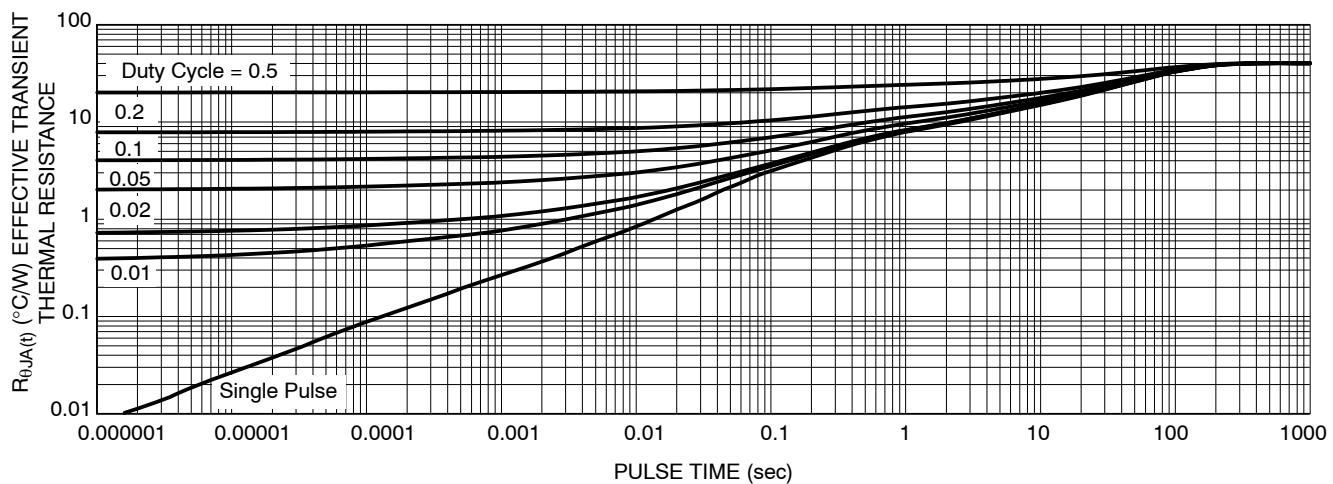
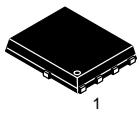


Figure 12. Thermal Response

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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SCALE 2:1

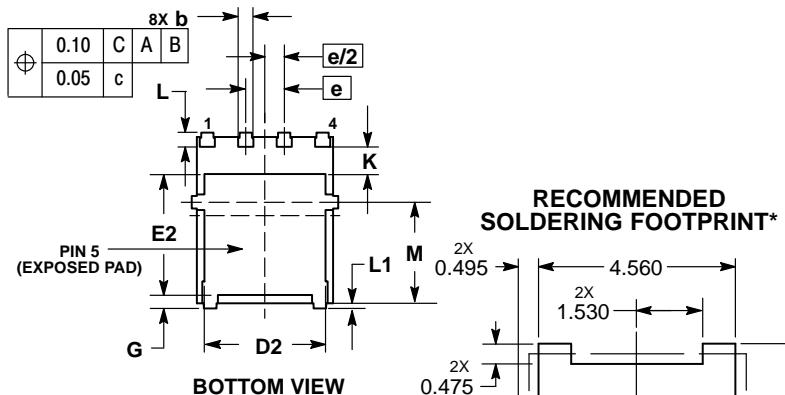
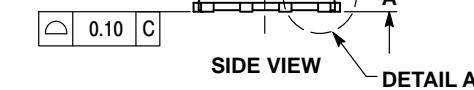
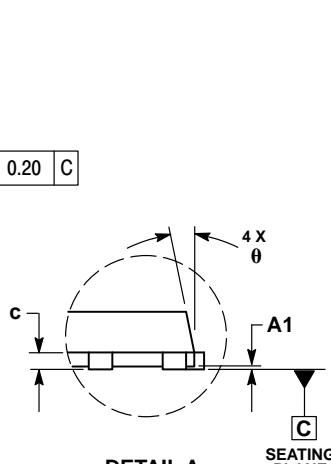
DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

NOTES:

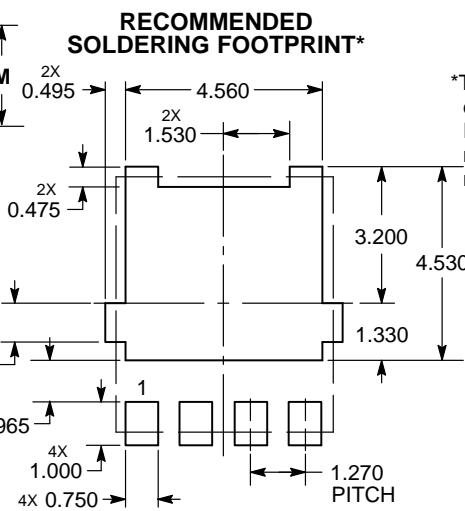
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	—	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	—	12 °



STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE



DIMENSIONS: MILLIMETERS

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code

A = Assembly Location

Y = Year

W = Work Week

ZZ = Lot Traceability

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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